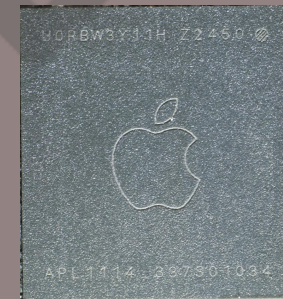
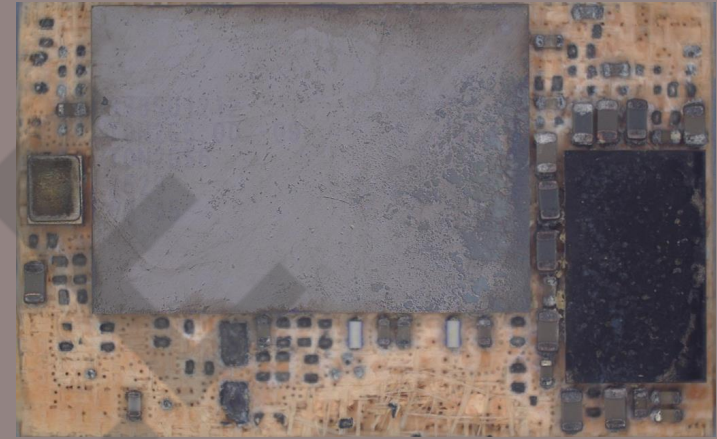


# Apple C1 & N1

Chip analyze

V1



@Kurnal

Apple N1

Apple C1X

Version	Date	Updates	Author
V0.1	2025/12/22 16:32	Working	Kurnal
V0.2	2025/12/22 19:26	Finish CI	Kurnal
VI	2025/12/26 23:27	Finish NI	Kurnal



This Report is made From @Kurnal  
Copyright @Kurnal

BiliBili: @Kurnal

X: @Kurnalsalts

WeChat: KurnalWeChat

# C1 Analyze

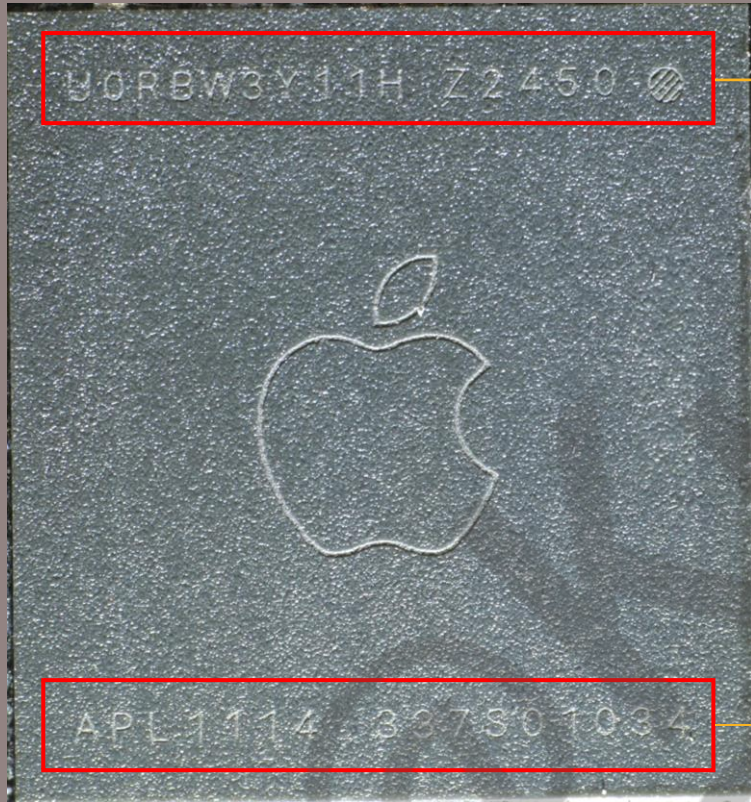
Package



APL1114 Frontside



APL1088 Frontside



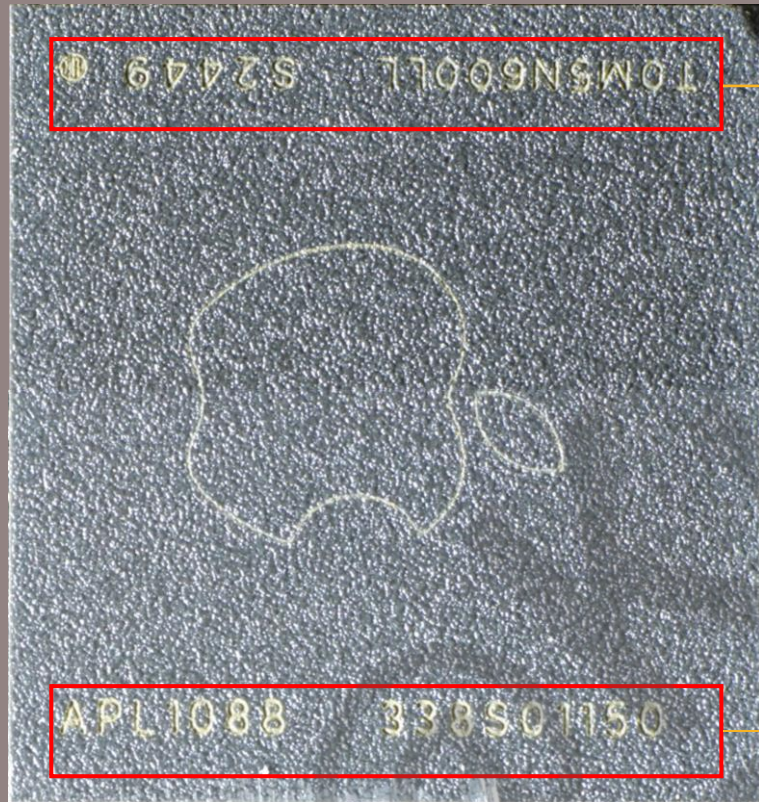
Product name:

APL 1114

Made/Package data:

Year 2024 Week 50

APL1114 Frontside



APL1088 Frontside



Product name:

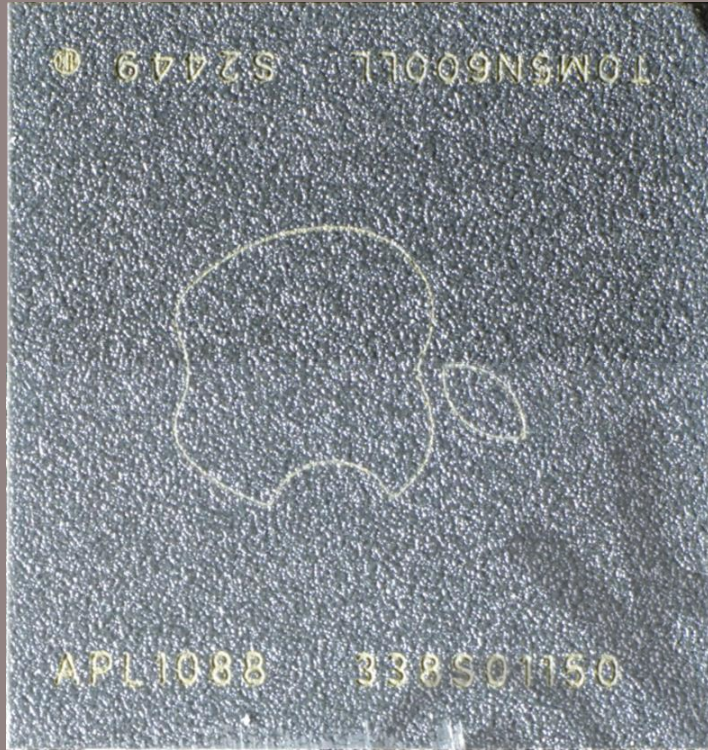
APL 1088

Made/Package data:

Year 2024 Week 49

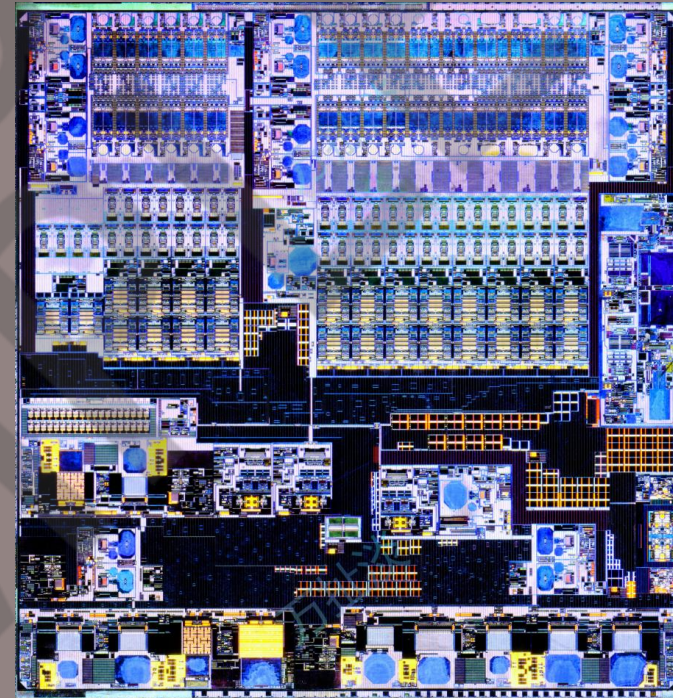
# C1 Analyze

Decap

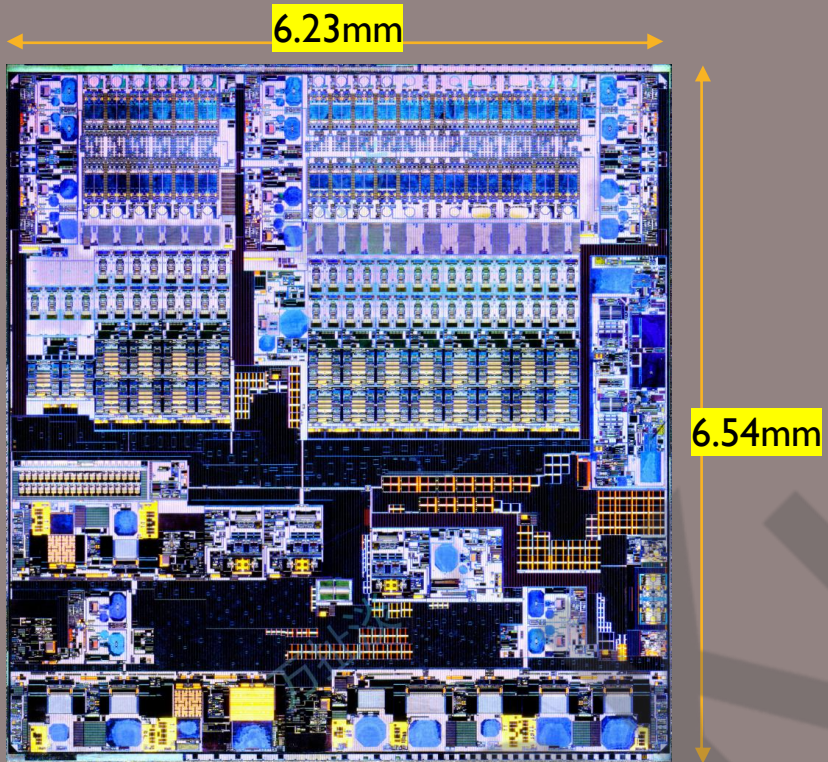


APL1088 Frontside

Decaped

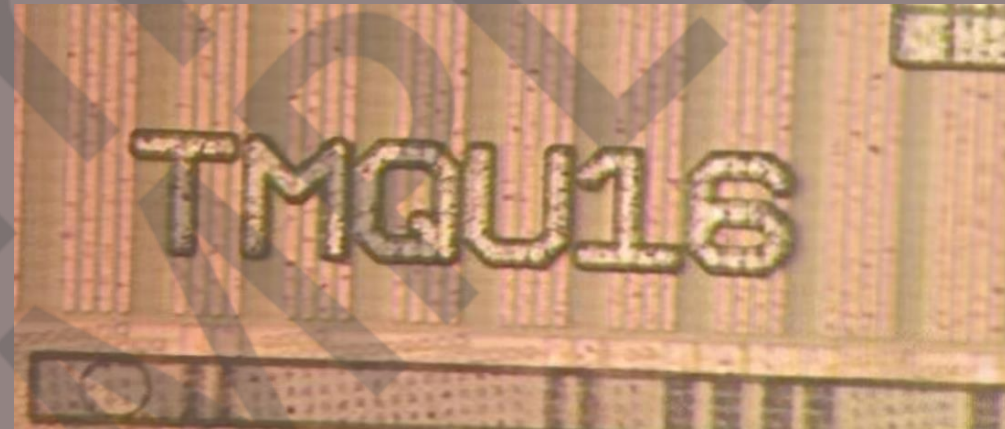


APL1088 Dieshot



APL1088 Dieshot

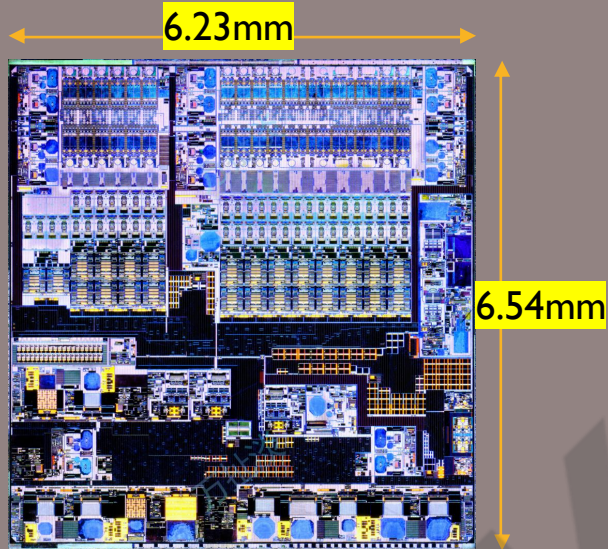
Die size: 40.7442mm<sup>2</sup>  
Die Thickness: 130um  
with out seal ring: 6.19mm x 6.38mm



Die Mark : TM QUI 6

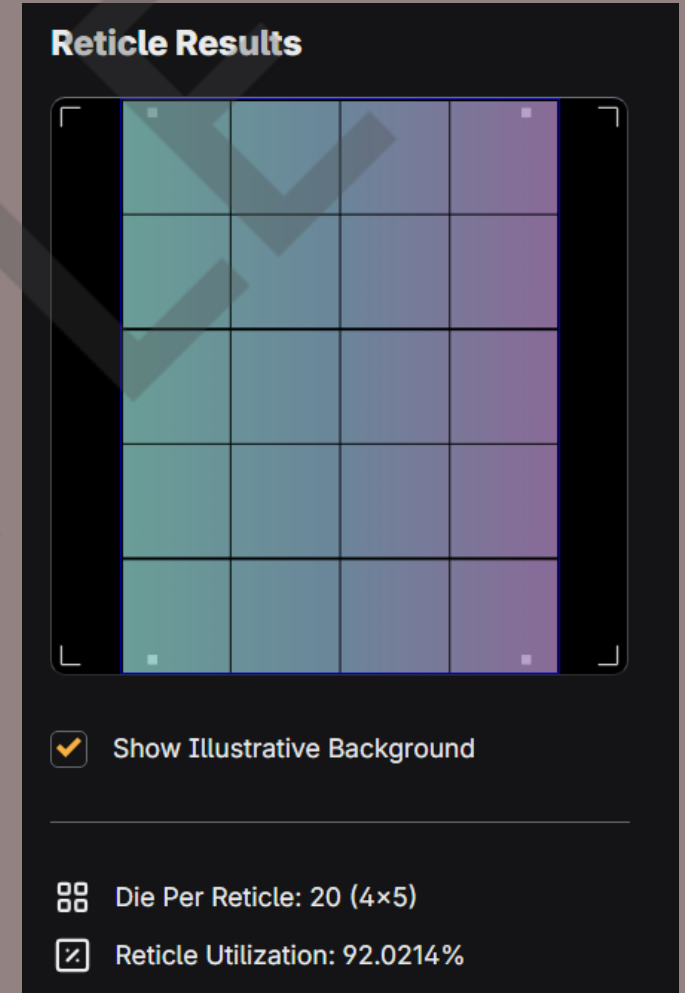
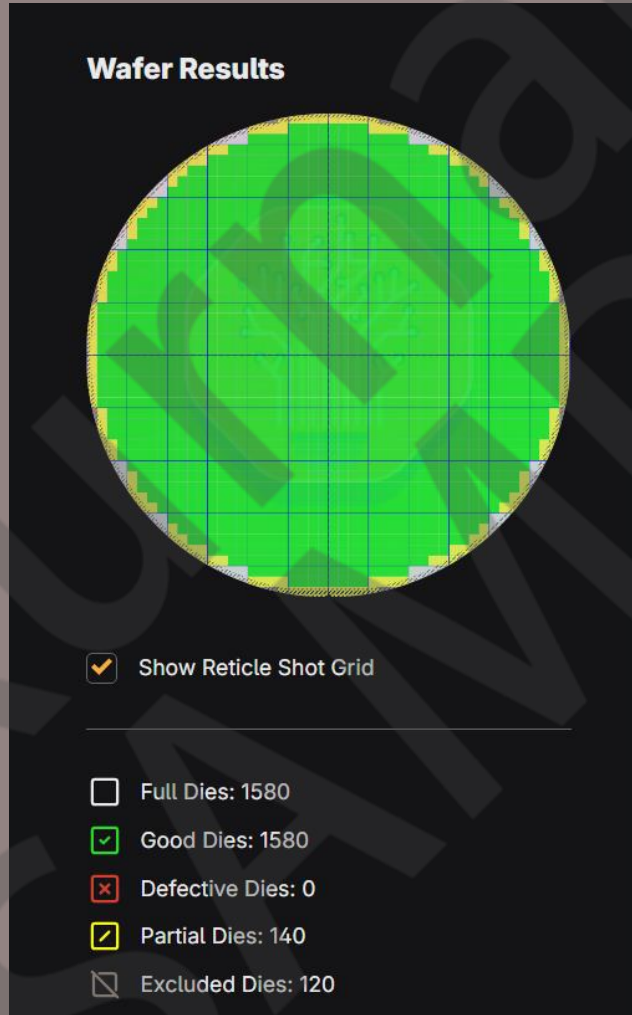


TSMC Tap Out Mark  
Tap Out in year 2022/2023



APL1088 Dieshot

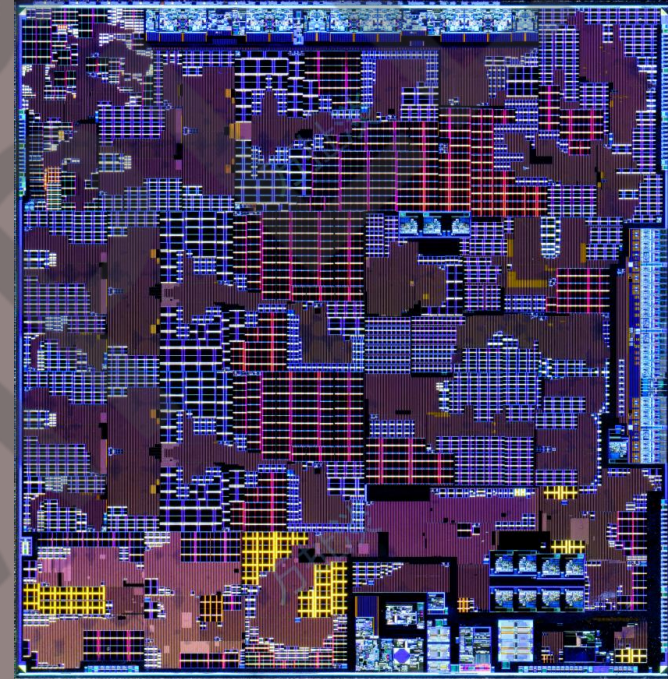
Die size: 40.7442mm<sup>2</sup>  
Die Per Wafer: 1580  
Die Per Mask: 20:1



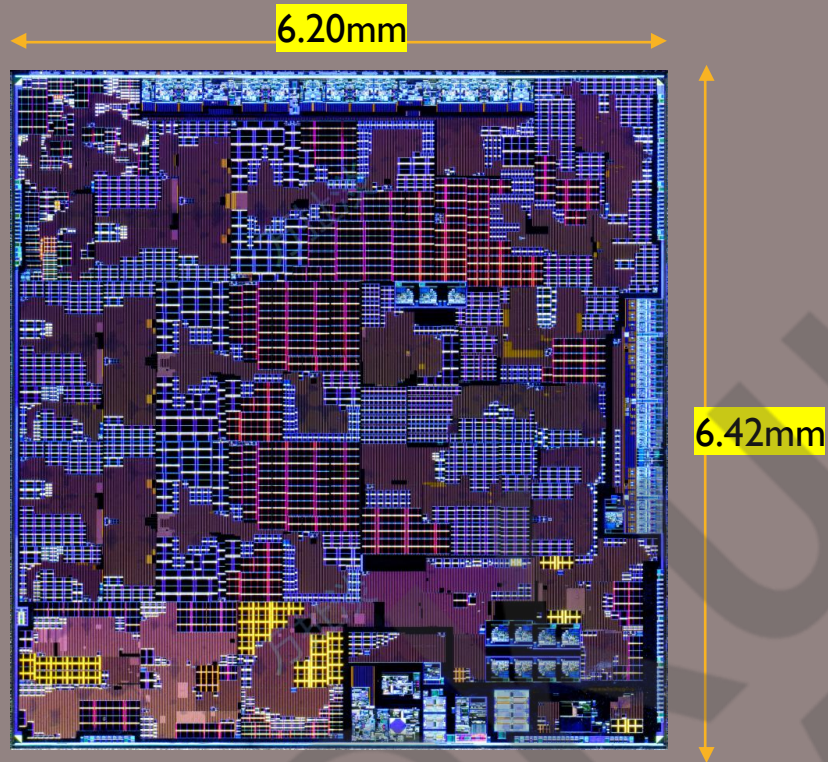


APL1114 Frontside

Decaped

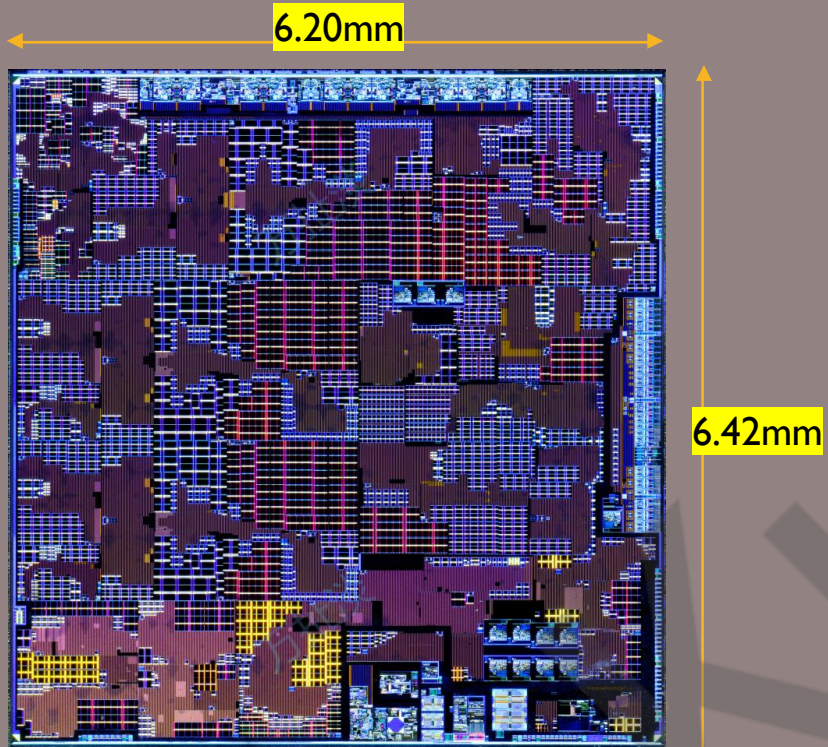


APL1114 Dieshot



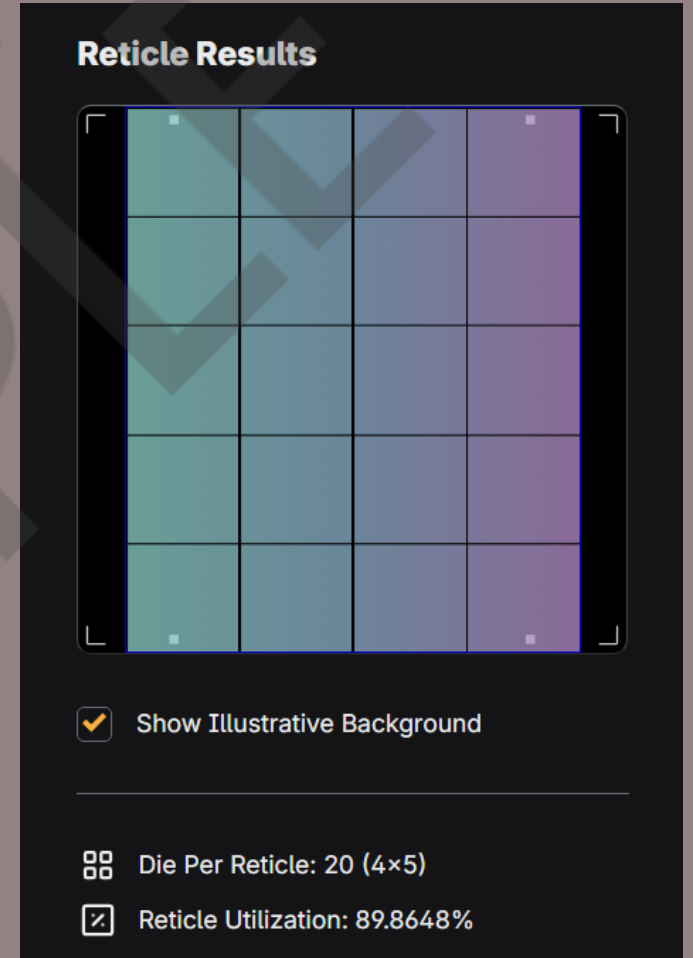
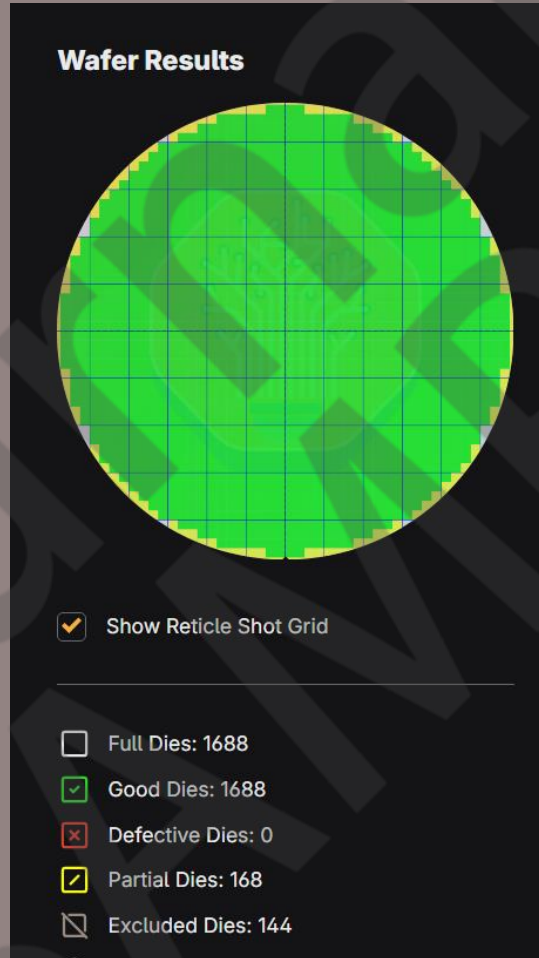
APL1114 Dieshot

Die size: 39.80mm<sup>2</sup>  
Die Thickness: 100um  
with out seal ring: 6.14mm x 6.32mm  
Die Mark : **Not Found**

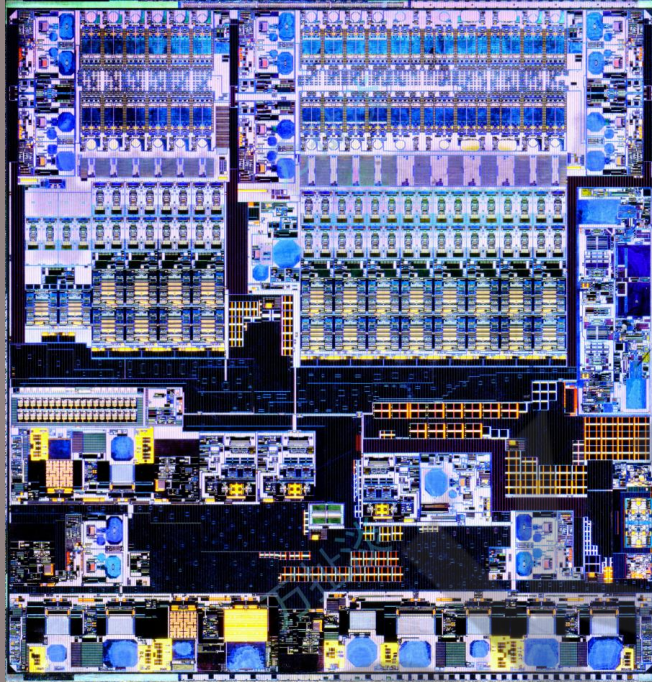


APL1114 Dieshot

Die size: 39.8mm<sup>2</sup>  
Die Per Wafer: 1688  
Die Per Mask: 20:1

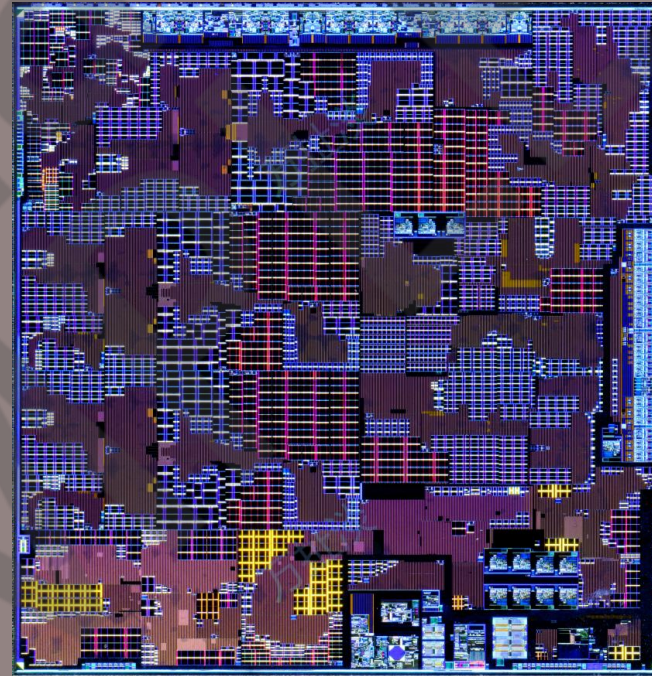


APL1088 Frontside



CI RF Chip

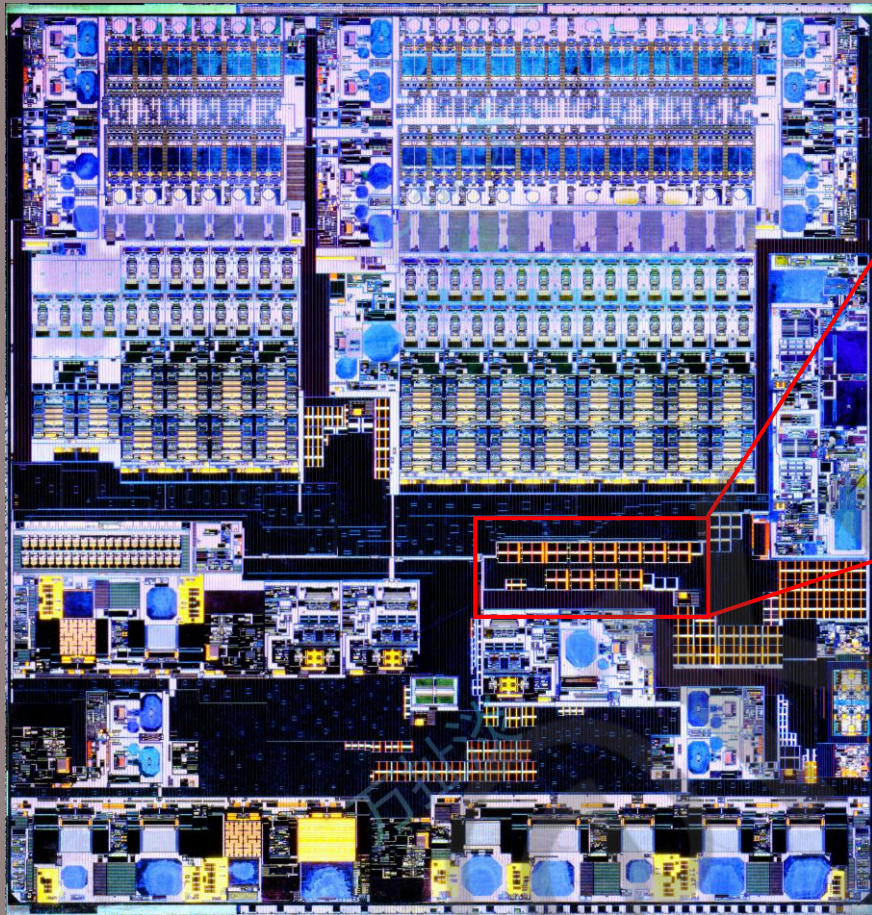
APL1114 Frontside



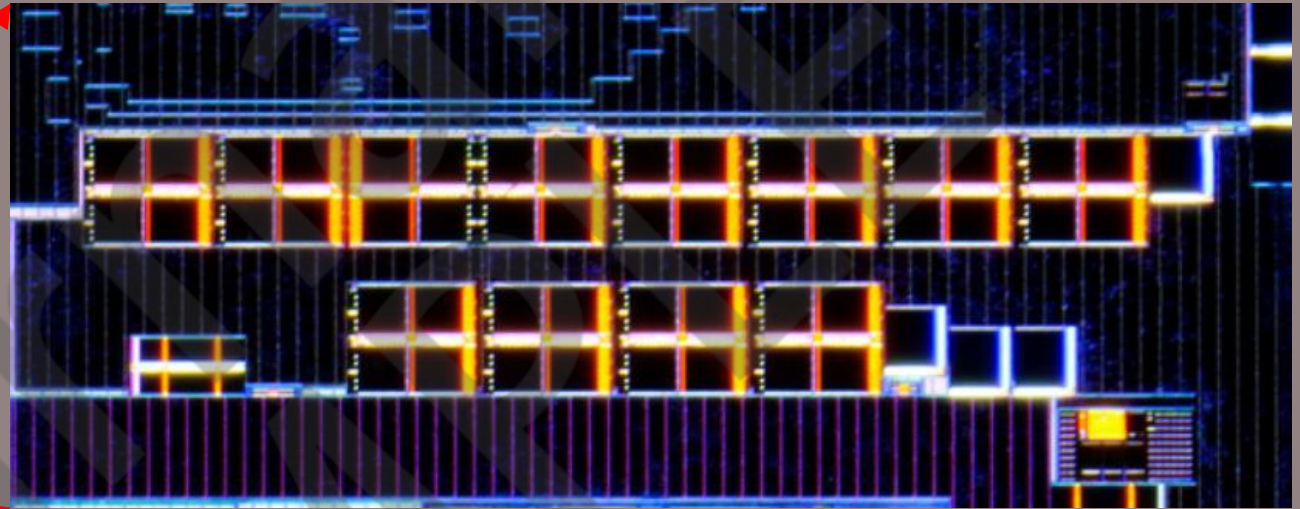
CI Modem Chip

# Process identification

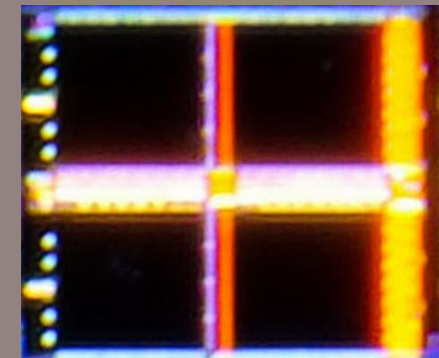
APL1088/APL1114

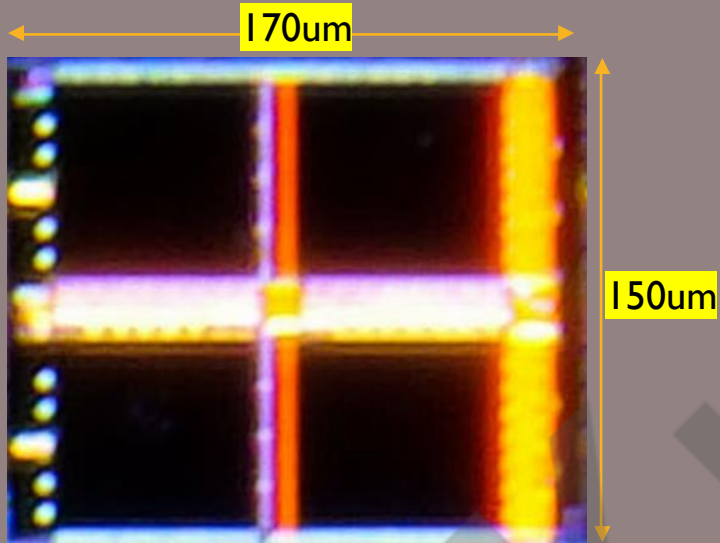


APL1088 Frontside



In APL1088, have some SRAM Block IP #1





64KiByte SRAM IP #1

Size: 64KiB

0.0255mm<sup>2</sup>/64KiB

2,509.80KiB/mm<sup>2</sup>

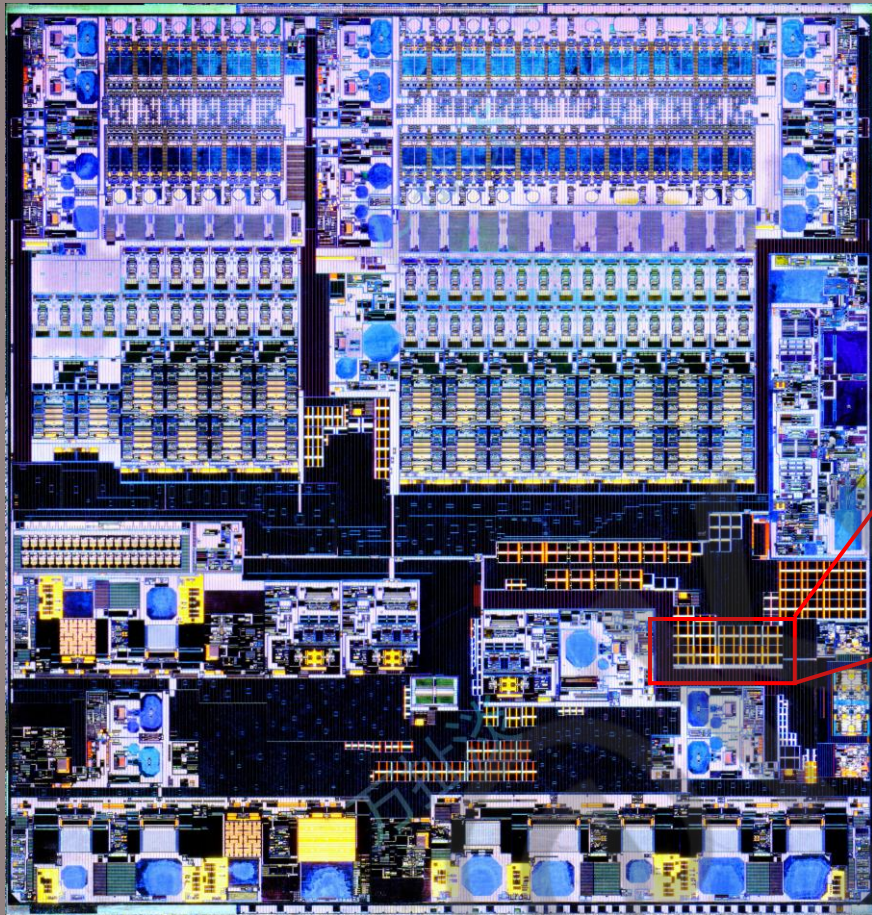
19.60Mbit/mm<sup>2</sup>



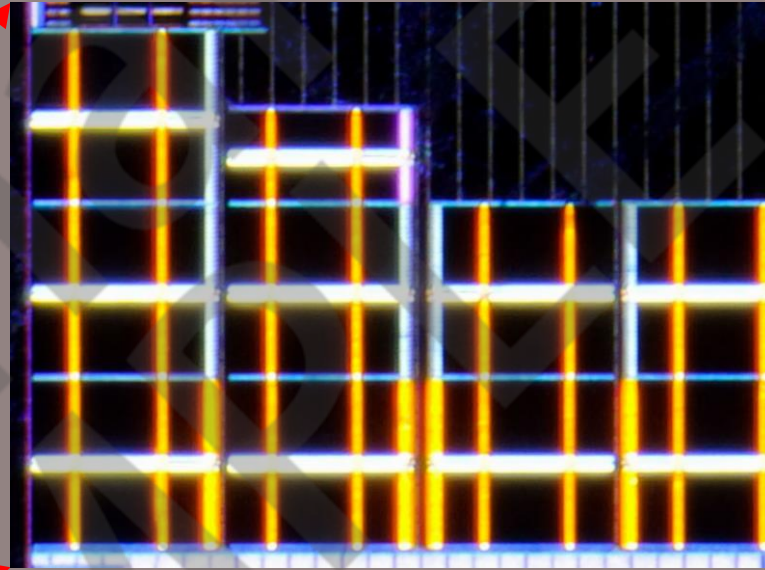
SRAM bit cell by used: 14,400um<sup>2</sup>

Proportion: 56.47%

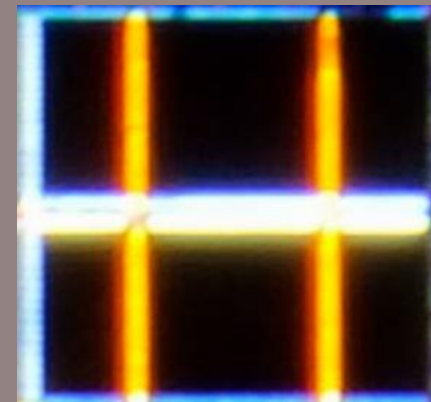
SRAM Bit cell Density: 0.027465um<sup>2</sup>/bit

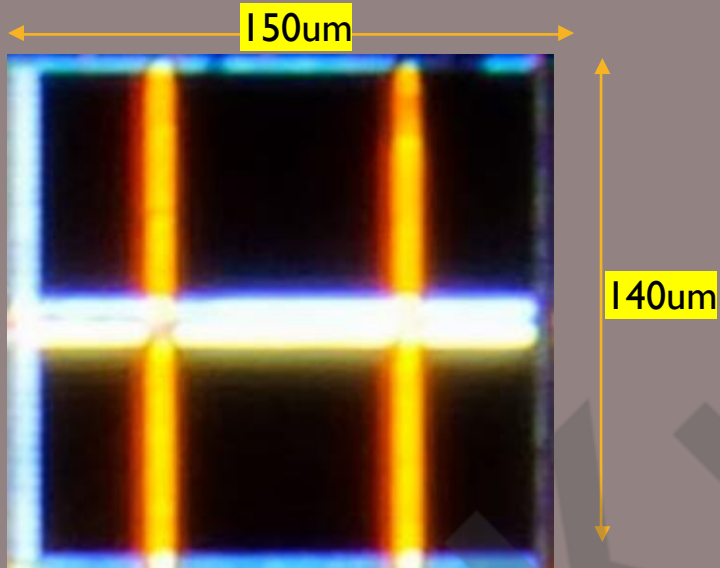


APL1088 Frontside



In APL1088 ,have some SRAM Block IP #2





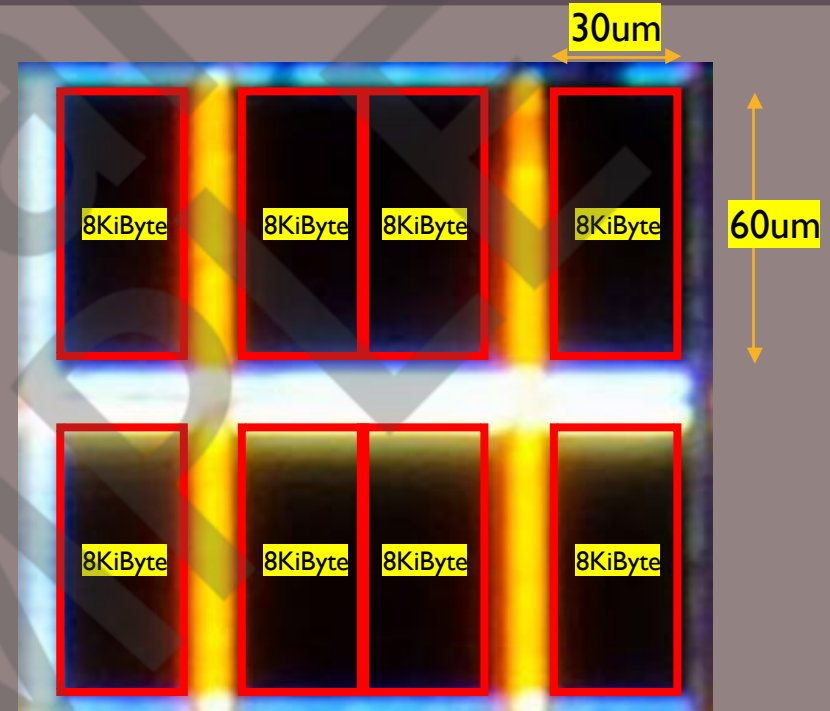
64KiByte SRAM IP #2

Size: 64KiB

0.021mm<sup>2</sup>/64KiB

3,047.61KiB/mm<sup>2</sup>

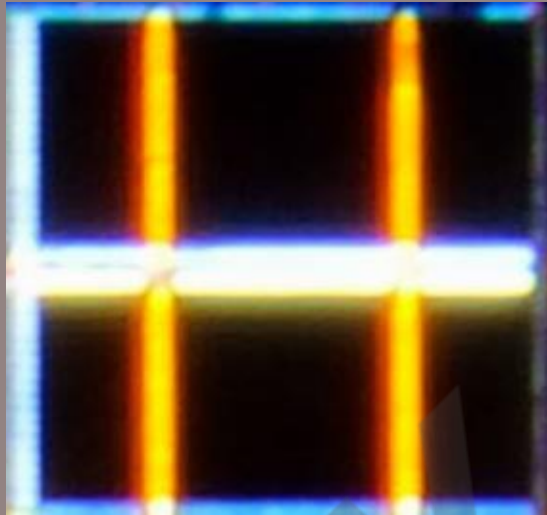
23.80Mbit/mm<sup>2</sup>



SRAM bit cell by used: 14,400um<sup>2</sup>

Proportion: 68.57%

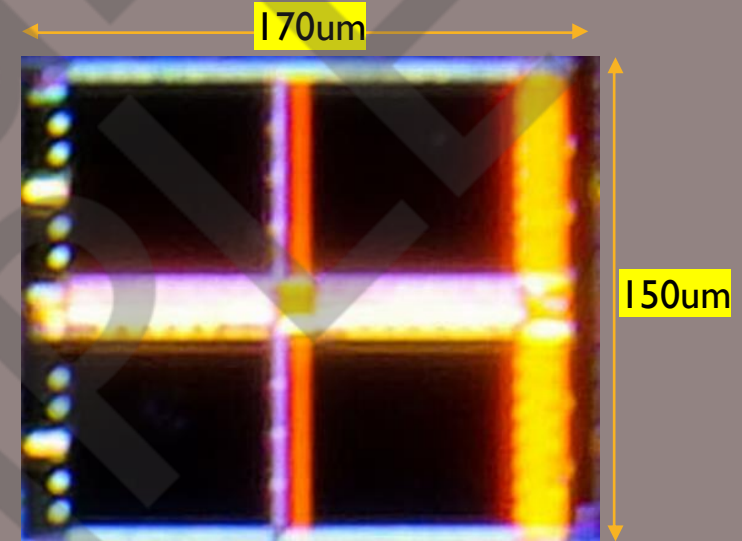
SRAM Bit cell Density: 0.027465um<sup>2</sup>/bit



APL1088 SRAM IP #2

SRAM Macro density: 23.8Mbit/mm<sup>2</sup>  
SRAM bit cell Density: 0.027465um<sup>2</sup>/bit

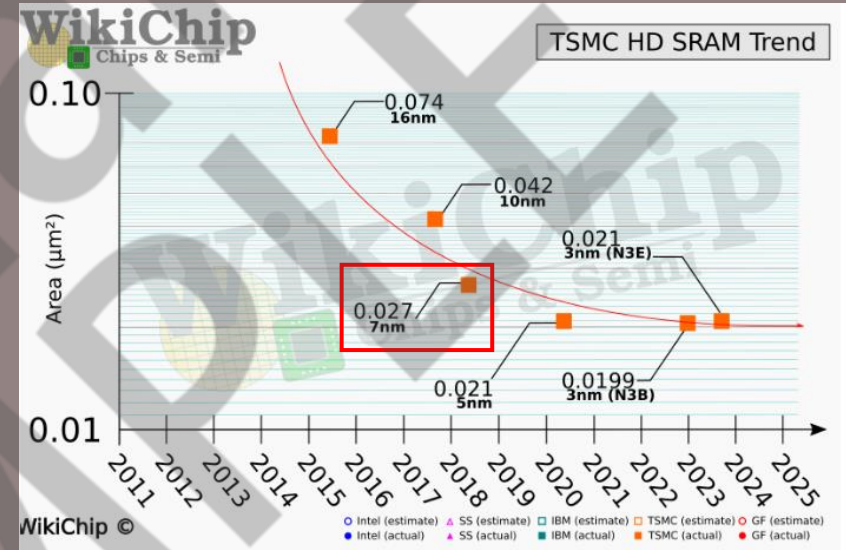
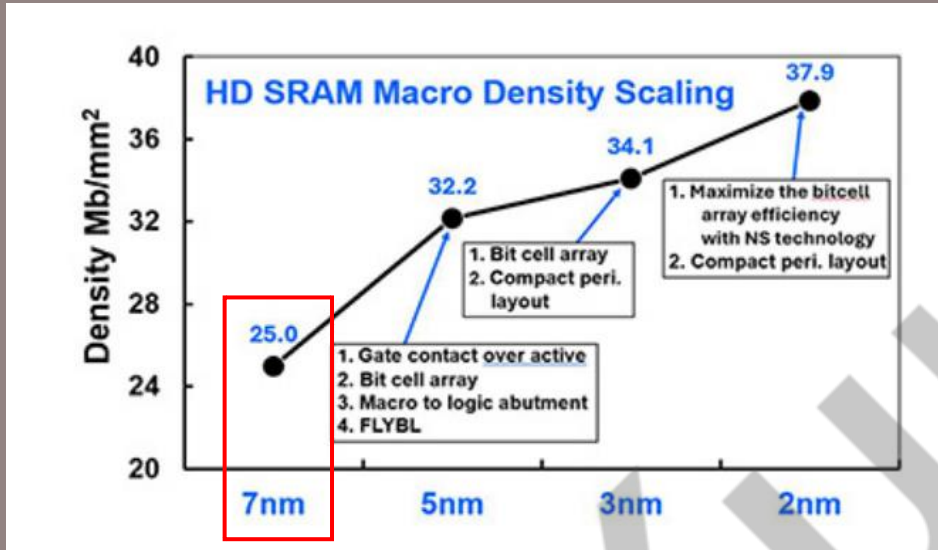
High Density SRAM Block?



APL1088 SRAM IP #1

SRAM Macro density: 19.6Mbit/mm<sup>2</sup>  
SRAM bit cell Density: 0.027455um<sup>2</sup>/bit

High Perf SRAM Block?



TSMC N7 SRAM Macro density: **25.0Mbit/mm2**

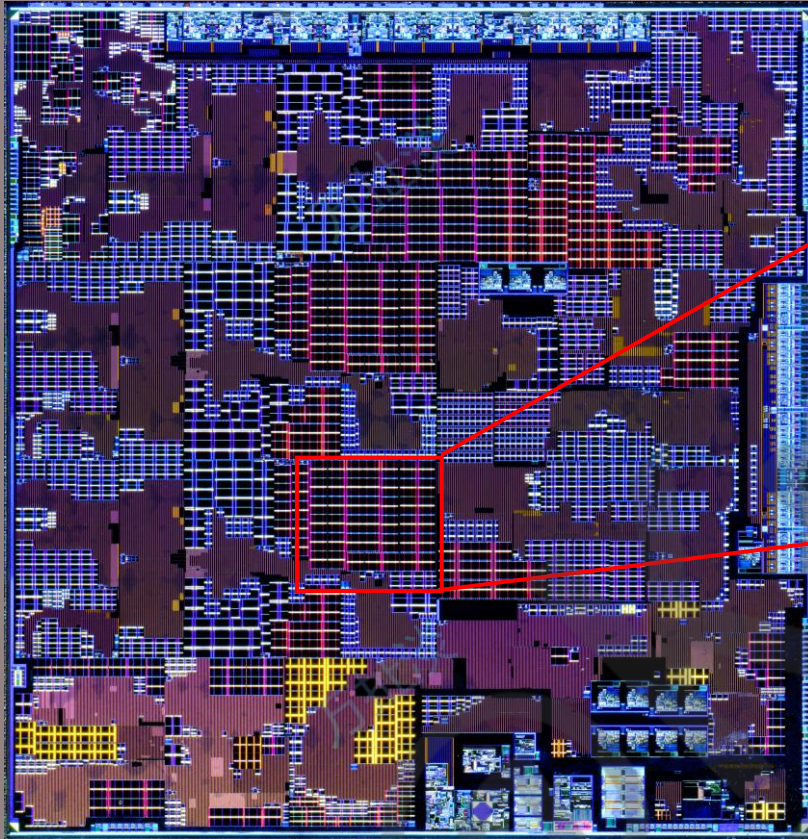
TSMC N7 SRAM bit cell density: **0.027um2/bit**



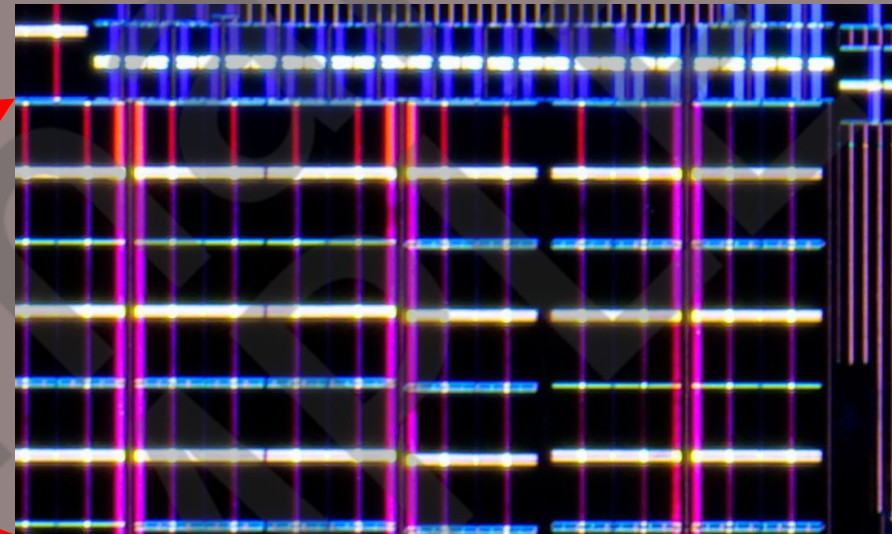
APL1088 SRAM IP #2

SRAM Macro density: **23.8Mbit/mm2**  
 SRAM bit cell density: **0.027465um2/bit**

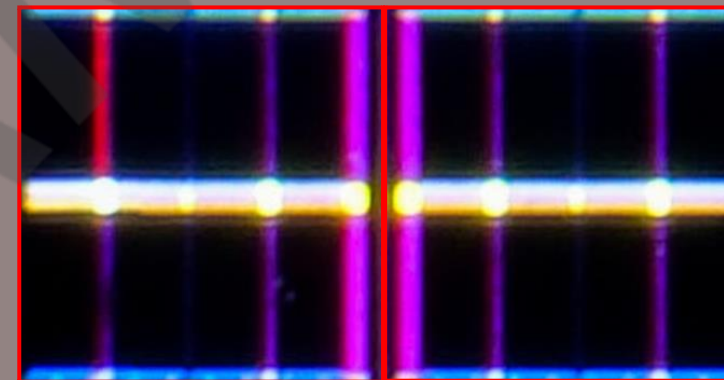
APPLE APL1088  
 Used TSMC **N7 Family**

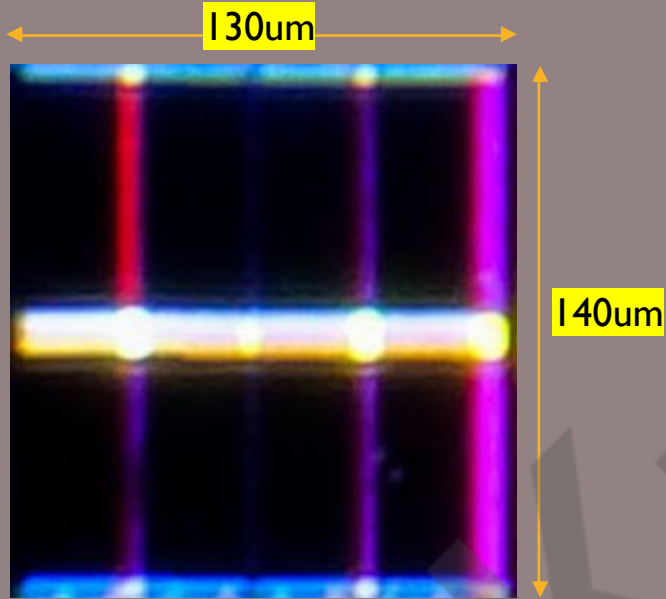


APL1114 Frontside



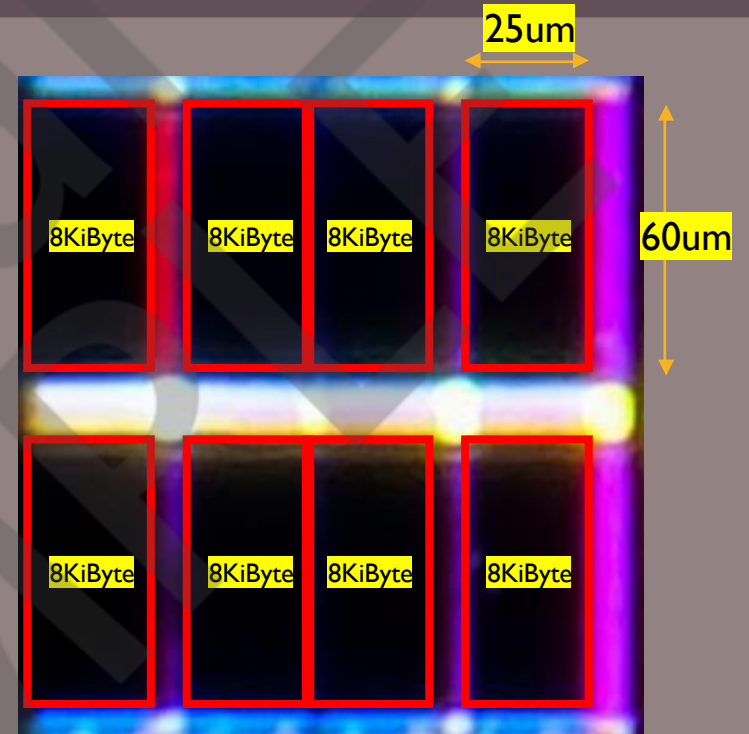
In APL1114, have some SRAM Block IP #3





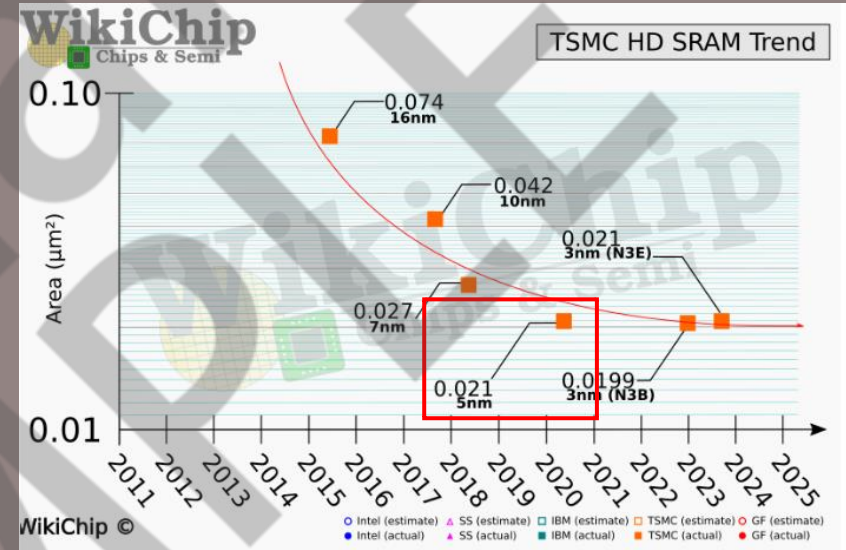
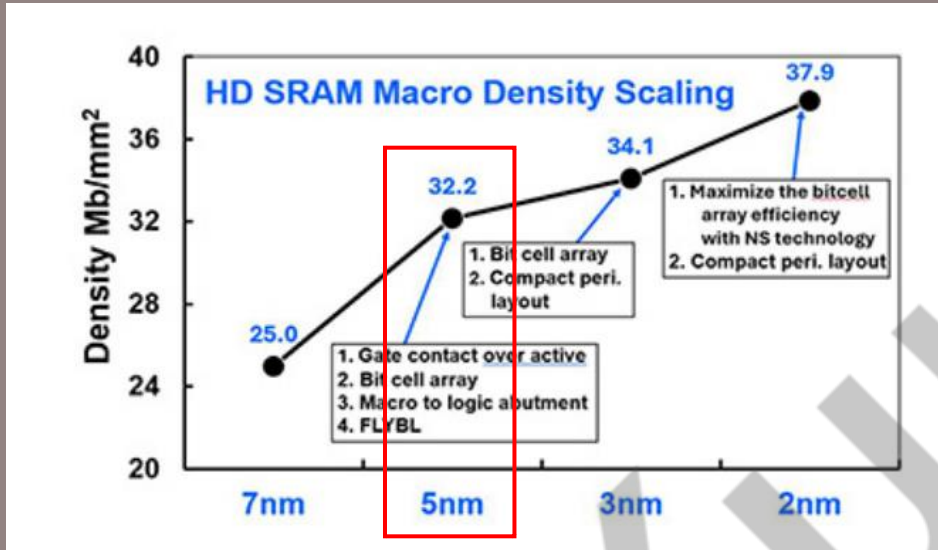
64KiByte SRAM IP #3  
Size: 64KiB

0.0182mm<sup>2</sup>/64KiB  
3,516.48KiB/mm<sup>2</sup>  
27.47Mbit/mm<sup>2</sup>



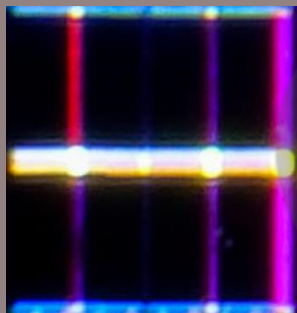
SRAM bit cell by used: 12,000um<sup>2</sup>  
Proportion: 65.93%

SRAM Bit cell Density: 0.02403um<sup>2</sup>/bit



TSMC N5 SRAM Macro density: **32.2Mbit/mm2**

TSMC N5 SRAM bit cell density: **0.021 µm2/bit**



APL1114 SRAM IP #3

SRAM Macro density:  
SRAM bit cell density:

Bigger than **N7 HD**  
Smaller than **N5 HD**

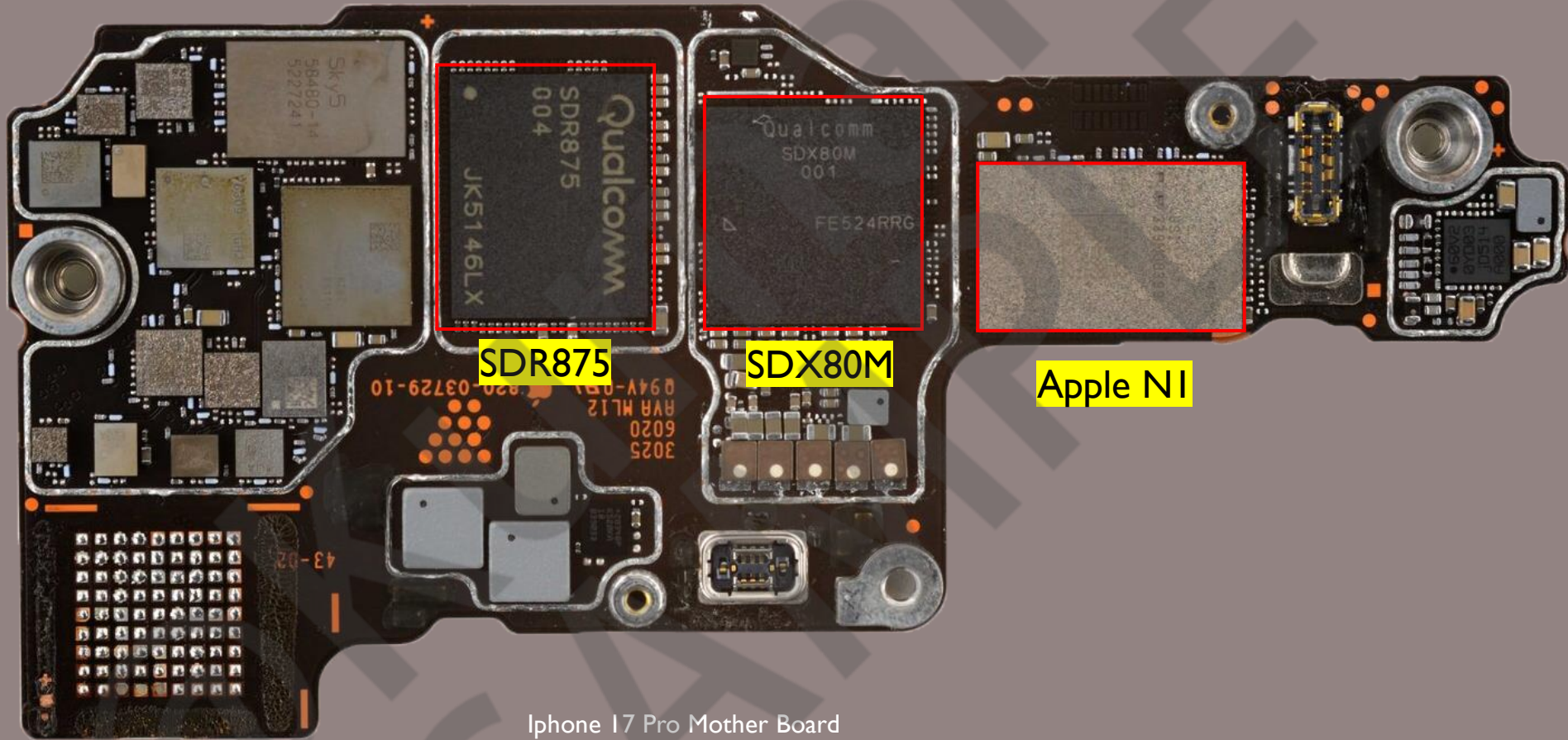
**27.47Mbit/mm2**  
**0.02403µm2/bit**

**APPLE APL1114**  
**Used TSMC N5 Family**

Bigger than **N7 HD**  
Smaller than **N5 HD**

# N1 Analyze

On chip analyze

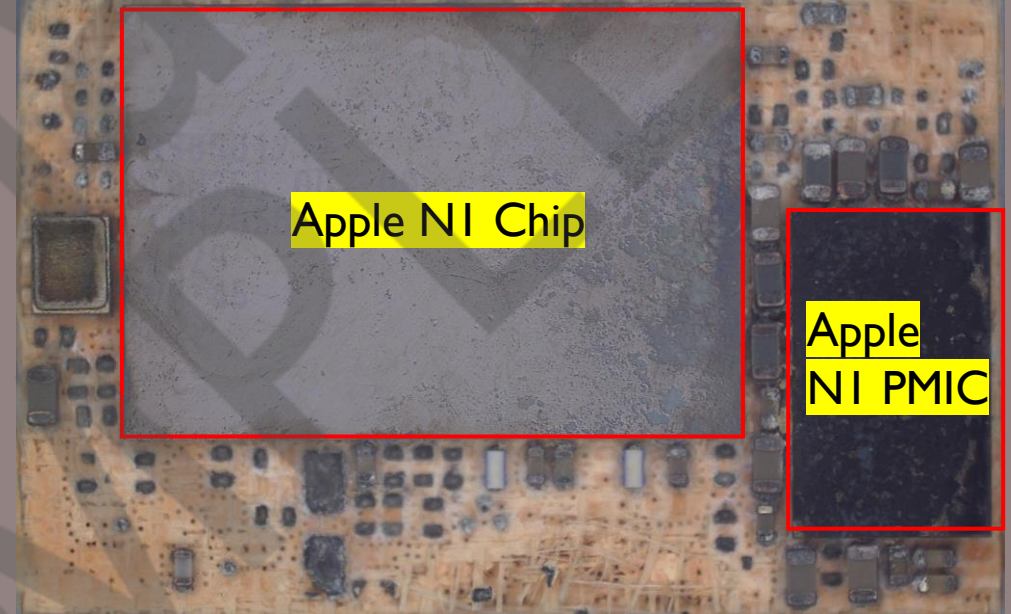


Iphone 17 Pro Mother Board



Apple N1 Package

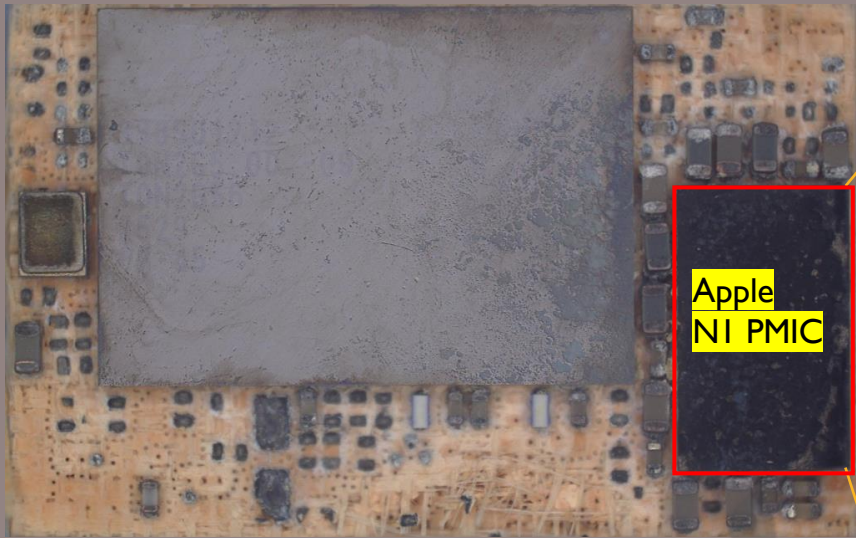
Decaped



Apple N1 Package

Used SiP (System in Package)

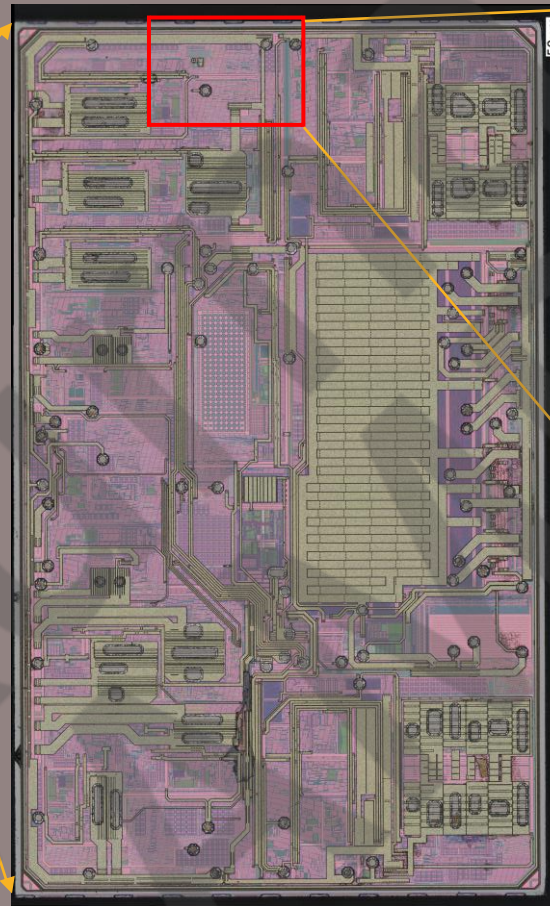
# N1 Analyze-Package-PMIC



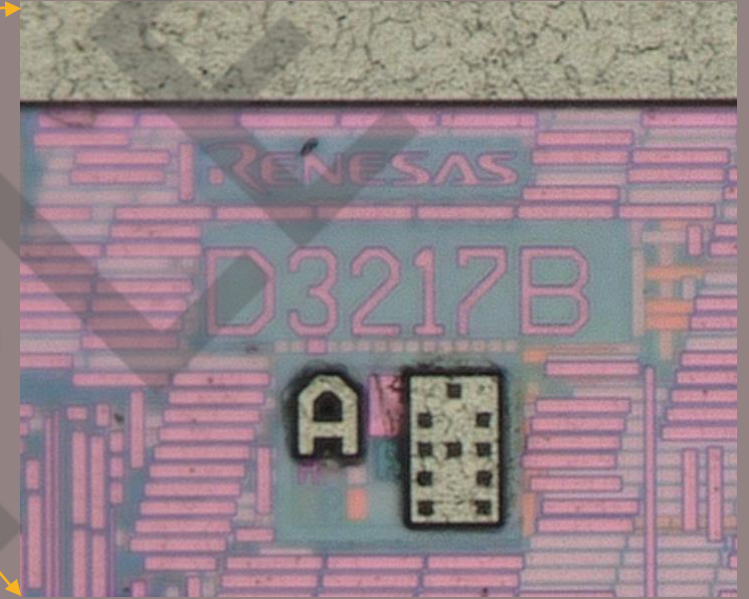
Apple NI Package

Die size: **6.73mm<sup>2</sup>** (2.02mm x 3.33mm)

Chip made by **RENESAS**



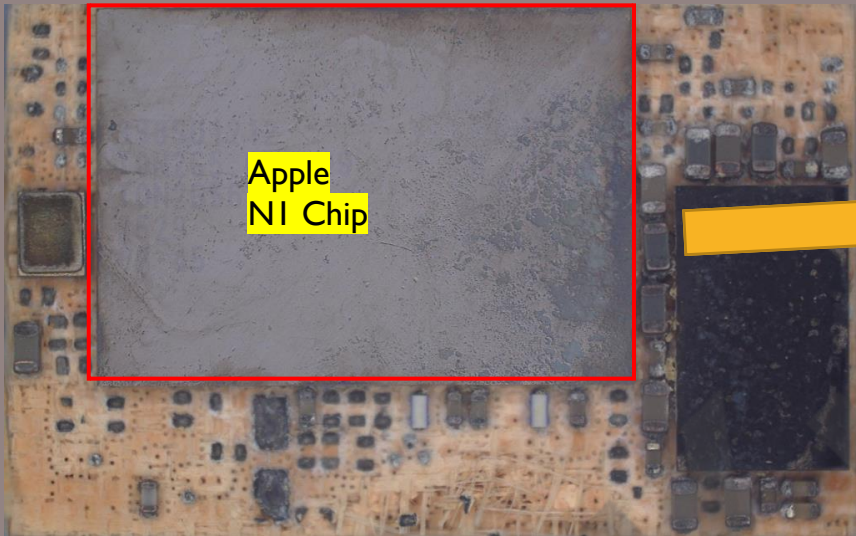
Apple NI PMIC



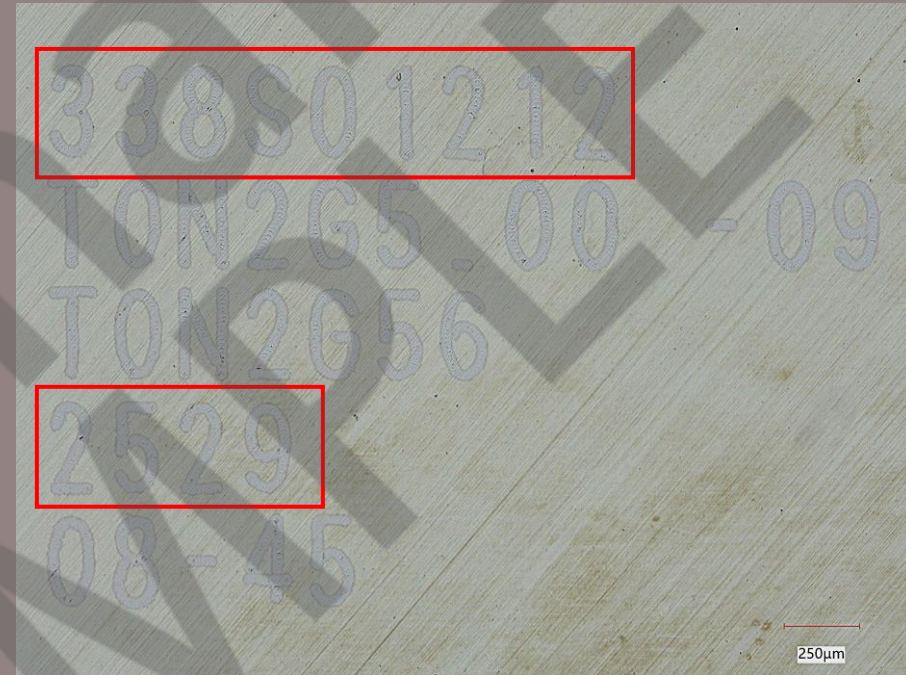
Apple NI PMIC Diemark

Die Mark: **Renesas D3217B**





Apple N1 Package



Apple N1 Top mark

Product name: **338S01212**

Made/Package data: **Year 2025 Week 29**



Apple N1 Dieshot

Die size: 27.8mm<sup>2</sup>  
with out seal ring: 6.20mm x 4.33mm



Apple N1 Diemark

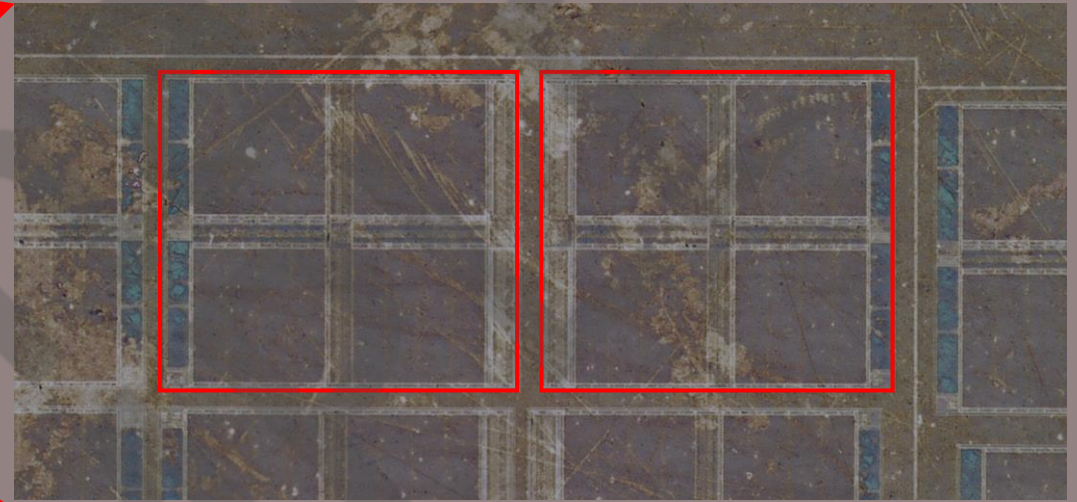
Die Mark : TM SX10



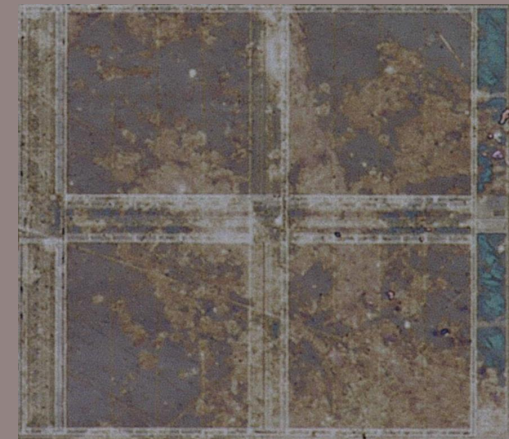
TSMC Tap Out Mark  
Tap Out in year 2024

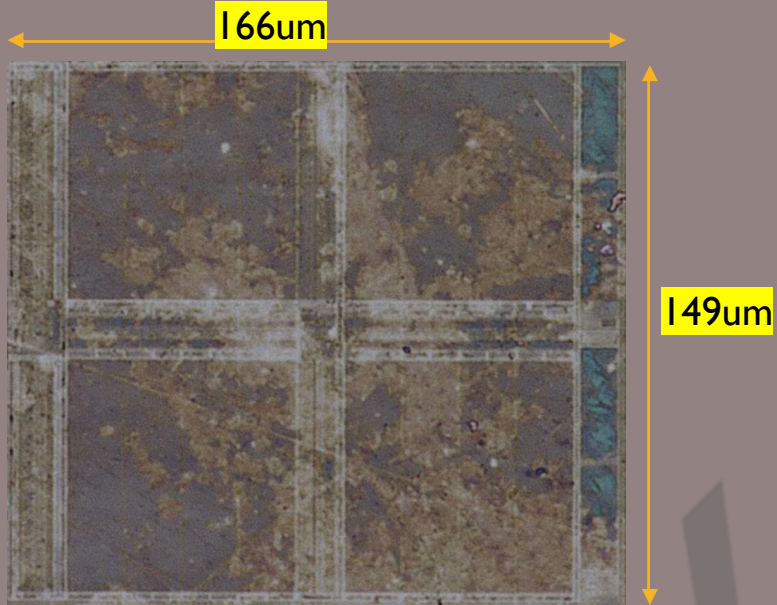


Apple N1 Dieshot



In Apple N1 ,have some SRAM Block IP #4





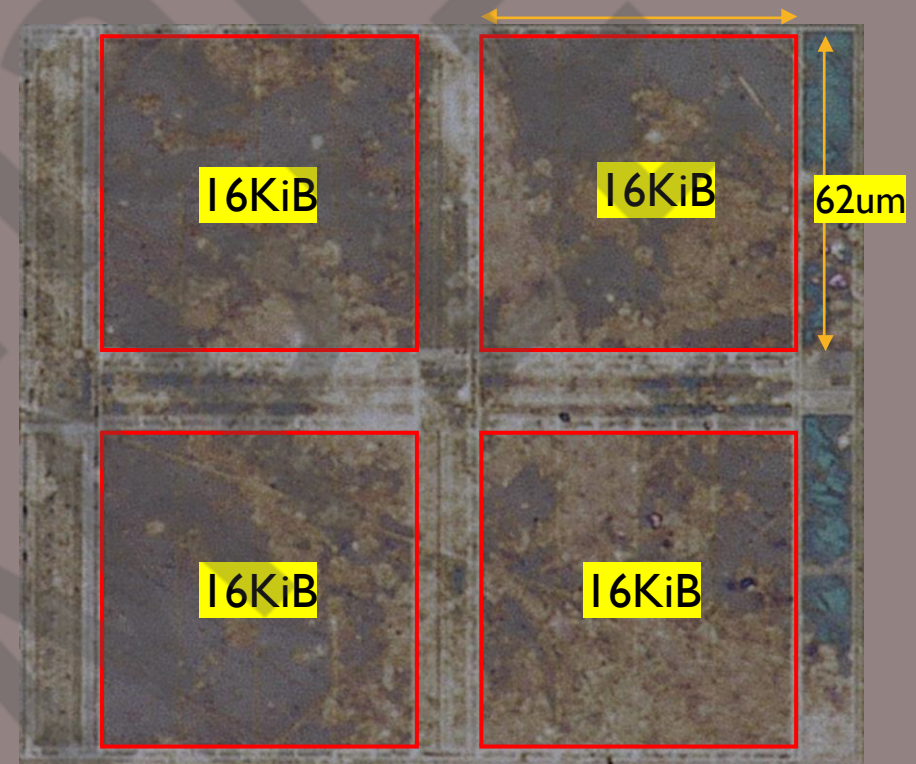
64KiByte SRAM IP #4

Size: 64KiB

0.024734mm<sup>2</sup>/64KiB

2,587.53KiB/mm<sup>2</sup>

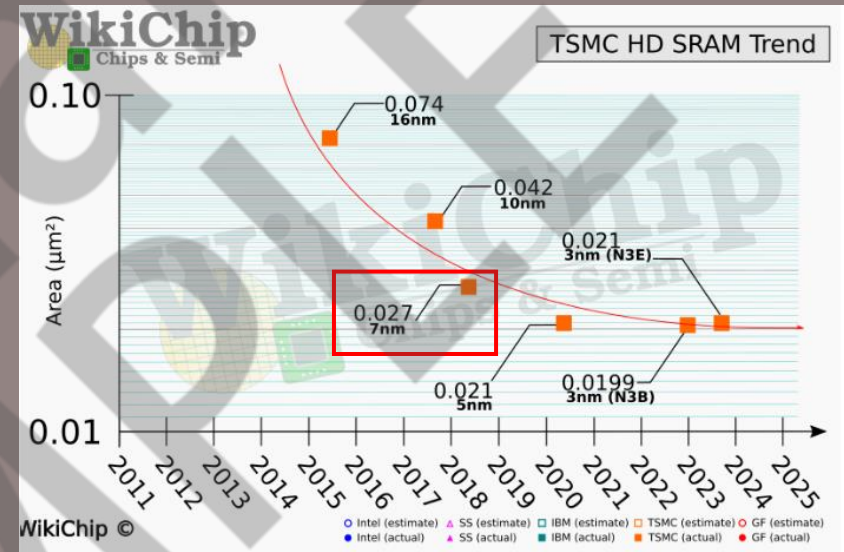
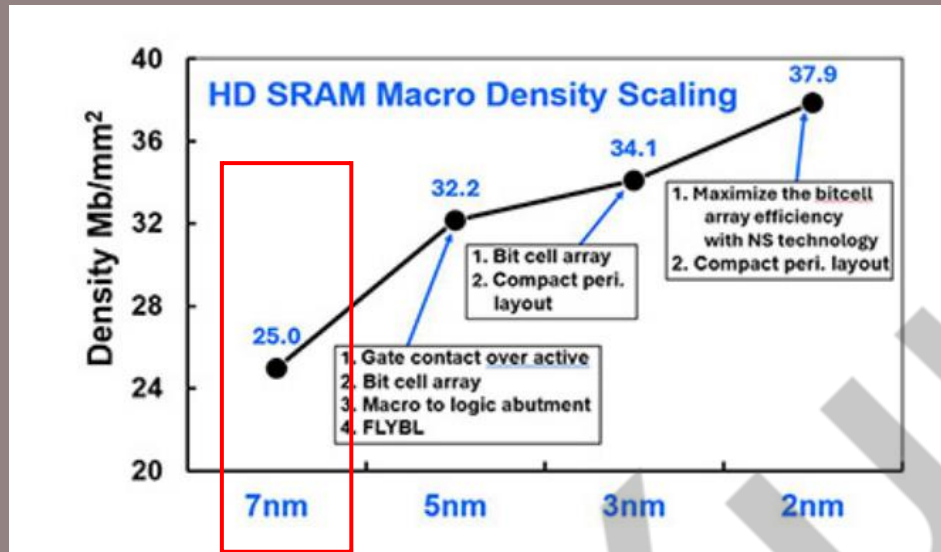
20.215Mbit/mm<sup>2</sup>



SRAM bit cell by used: 15,376um<sup>2</sup>

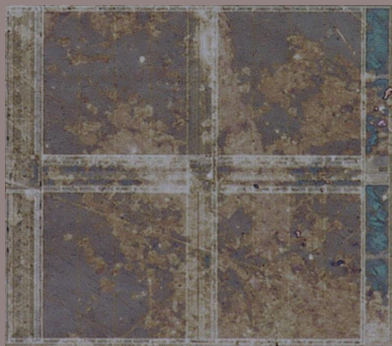
Proportion: 62.165%

SRAM Bit cell Density: 0.029327um<sup>2</sup>/bit



TSMC N7 SRAM Macro density: **25.0Mbit/mm<sup>2</sup>**

TSMC N7 SRAM bit cell density: **0.027µm<sup>2</sup>/bit**



Apple N1 SRAM IP #4

Bigger than **N7 HD**

SRAM Macro density: **20.215Mbit/mm<sup>2</sup>**

SRAM bit cell density: **0.029327µm<sup>2</sup>/bit**

**APPLE N1**  
Used TSMC **N7 HP**

Bigger than **N7 HD**